N-Channel 150-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

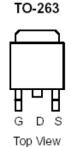
Typical Applications:

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY				
Vds (V)	I⊳(A)			
150	200 @ V _{GS} = 10V	21 ^a		
150	225 @ V _{GS} = 5.5V	21		

in





ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)							
Parameter			Limit	Units			
Drain-Source Voltage			150	V			
Gate-Source Voltage	V _{GS}	±20	v				
Continuous Drain Current ^a	T _C =25°C	I _D	21	А			
Pulsed Drain Current ^b		I _{DM}	80	~			
Continuous Source Current (Diode Conduction) ^a		I _S	110	А			
Power Dissipation ^a	T _C =25°C	PD	300	W			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150	°C			

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
Maximum Junction-to-Ambient ^a	$R_{ extsf{ heta}JA}$	62.5	°C/W			
Maximum Junction-to-Case	$R_{ extsf{ heta}JC}$	1	0/11			

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

Parameter	Symbol	Min	Тур	Мах	Unit			
Static								
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \text{ uA}$	1			V		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$			±100	nA		
Zero Gate Voltage Drain Current		$V_{DS} = 120 V, V_{GS} = 0 V$	1 25		1	uA		
	I _{DSS}	$V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25			
On-State Drain Current	I _{D(on)}	$V_{DS} = 5 V, V_{GS} = 10 V$	30			А		
Drain-Source On-Resistance	r _{max} ,	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 16.8 \text{ A}$			200	mΩ		
Diam-Source On-Resistance	r _{DS(on)}	$V_{GS} = 5.5 \text{ V}, \text{ I}_{D} = 13.4 \text{ A}$			225	11122		
Forward Transconductance	g _{fs}	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 20 \text{ A}$		24		S		
Diode Forward Voltage	V_{SD}	$I_{S} = 30 \text{ A}, V_{GS} = 0 \text{ V}$		0.99		V		
		Dynamic						
Total Gate Charge	Qg	V _{DS} = 50 V, V _{GS} = 5.5 V,		11		nC		
Gate-Source Charge	Q_gs	$V_{\rm DS} = 30 V, V_{\rm GS} = 3.3 V,$ $I_{\rm D} = 16.8 {\rm A}$		3.6				
Gate-Drain Charge	Q_{gd}	1 <u>0</u> - 10.0 A		4.3				
Turn-On Delay Time	t _{d(on)}	V _{DS} = 75 V, R _L = 4.4 Ω,		16				
Rise Time	t _r	$V_{DS} = 75 V, R_{L} = 4.4 \Omega,$ $I_{D} = 16.8 A,$		24				
Turn-Off Delay Time	t _{d(off)}	$V_{GEN} = 10 \text{ V}, \text{ R}_{GEN} = 6 \Omega$		32		ns		
Fall Time	t _f	$v_{\text{GEN}} = 10$ v_{c} $n_{\text{GEN}} = 0.22$		20				
Input Capacitance	C _{iss}			1233				
Output Capacitance	C _{oss}	V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz		59		рF		
Reverse Transfer Capacitance	C _{rss}			38				

Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

Analog Power (APL) reserves the right to make changes without further notice to any products herein. APL makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does APL assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in APL data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. APL does not convey any license under its patent rights nor the rights of others. APL products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the APL product could create a situation where personal injury or death may occur. Should Buyer purchase or use APL products for any such unintended or unauthorized application, Buyer shall indemnify and hold APL and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that APL was negligent regarding the design or manufacture of the part. APL is an Equal Opportunity/Affirmative Action Employer.

4

1

1.2

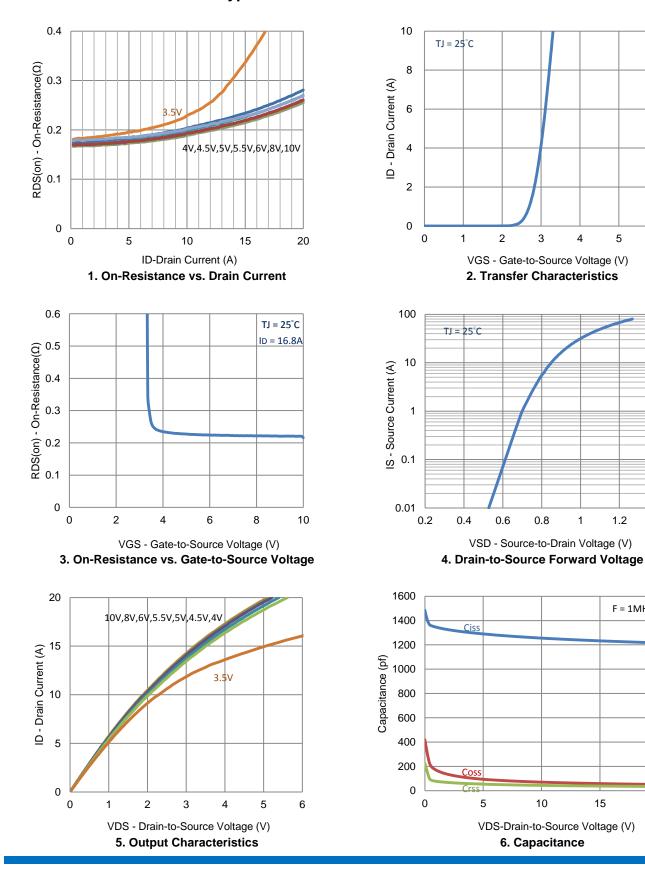
F = 1MHz

1.4

20

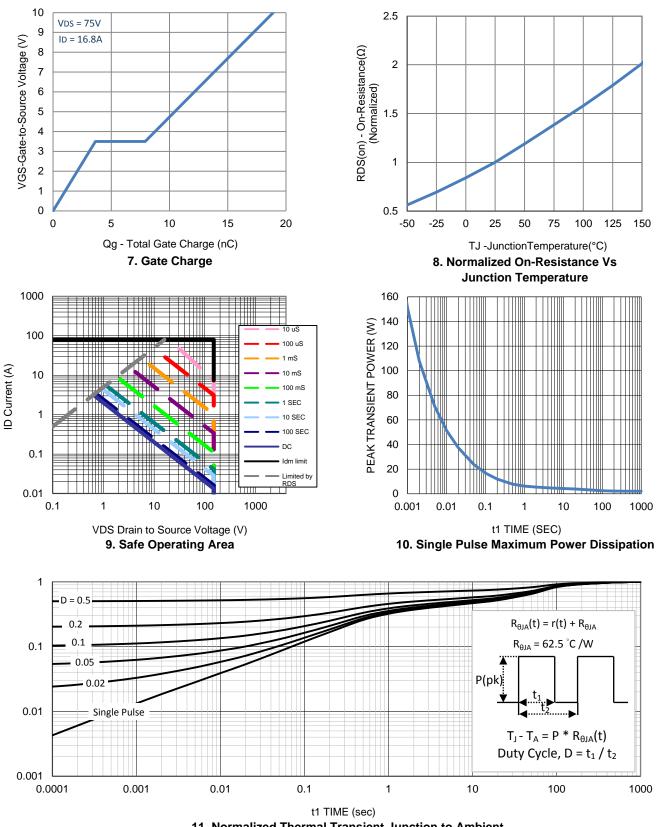
5

6



Typical Electrical Characteristics

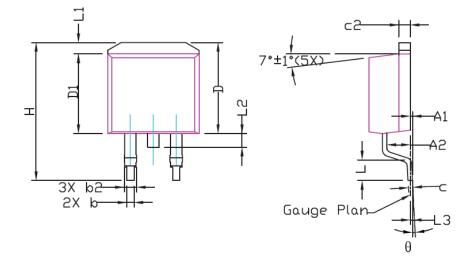
15

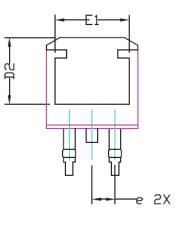


Typical Electrical Characteristics

11. Normalized Thermal Transient Junction to Ambient

Package Information





	DIMENS	IONAL F	REQMTS	INCH	ES REG	MTS	
SYMBOL	MIN	NDM	MAX	MIN	NDM	MAX	
A	4,30	4.57	4,72	0.169	0.180	0.186	
A1	0		0.25	0		0.010	
A2	2,47	2,57	2,67	0.097	0.101	0.105	
b	0.69	0.813	0.94	0.027	0.032	0.037	
b2	1.17	1.27	1,45	0.046	0.050	0.057	
С	0.48	0,50	0.60	0.019	0.020	0.024	
c2	1,17	1.27	1.37	0.046	0.050	0,054	
D	9,80	10.05	10.30	0.386	0,396	0.406	
D1	8,64	8.78	9,65	0.340	0.346	0,380	
D2	7,12	7.37	7,62	0.280	0,290	0,300	
E	9,70	10.15	10.54	0,382	0.400	0,415	
E1	8,00	8,20	8,40	0.315	0.323	0.331	
e	2.54 BSC			0.3	0.100 BSC		
Н	14.99	15.24	15,49	0.590	0.600	0.610	
L	1.78	2.29	2.79	0.070	0.090	0.110	
L1	1.02	1.27	1.52	0.040	0.050	0,060	
L2			1.75			0.069	
L3		0,254			0.010		
θ	0*		8*	0*		8*	